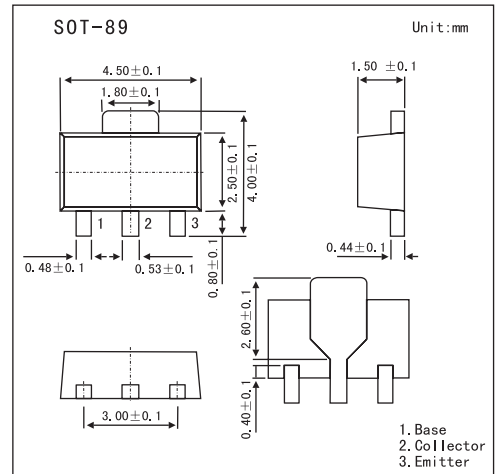


2SD1619

■ Features

- Very small size making it easy to provide highdensity, small-sized hybrid ICs.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	25	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	1	A
Collector current (pulse)	I _{CP}	2	A
Collector dissipation	P _C	500	mW
	P _C *	1.3	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Mounted on ceramic board(250mm2X0.8mm)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	V _{CB} = 20 V, I _E =0			0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 4 V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} = 2 V, I _C = 50 mA	100		560	
Gain bandwidth product	f _T	V _{CE} = 10 V, I _C = 50 mA		180		MHz
Output capacitance	C _{ob}	V _{CB} = 10 V, f = 1.0MHz		15		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500 mA, I _B = 50 mA		0.1	0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 500 mA, I _B = 50 mA		0.85	1.2	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5			V

■ hFE Classification

Marking	DB			
Rank	R	S	T	U
hFE	100~200	140~280	200~400	280~560